

# PJD90P03E-AU

## 30V P-Channel Enhancement Mode MOSFET

Voltage

-30 V

Current

-88 A

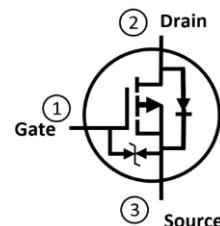
### Features

- $R_{DS(ON)}$ ,  $V_{GS} @ -10V$ ,  $I_D @ -20A < 6.4m\Omega$
- $R_{DS(ON)}$ ,  $V_{GS} @ -4.5V$ ,  $I_D @ -10A < 10.4m\Omega$
- 100% UIS tested
- Reliable and Rugged
- AEC-Q101 qualified
- Lead free in compliance with EU RoHS 2.0
- Green molding compound as per IEC 61249 standard

### Mechanical Data

- Case : TO-252AA Package
- Terminals : Solderable per MIL-STD-750, Method 2026
- Approx. Weight : 0.3217 grams

TO-252AA



### Maximum Ratings and Thermal Characteristics ( $T_A=25^\circ C$ unless otherwise noted)

| PARAMETER   | SYMBOL              | LIMIT           | UNITS        |
|---|---------------------|-----------------|--------------|
| Drain-Source Voltage                              | $V_{DS}$            | -30             | V            |
| Gate-Source Voltage                               | $V_{GS}$            | $\pm 25$        |              |
| Continuous Drain Current <sup>(Note 3)</sup>      | $I_D$               | -88             | A            |
|   |                     | -62             |              |
| Pulsed Drain Current <sup>(Note 1)</sup>          | $I_{DM}$            | -219            | W            |
| Power Dissipation                                 | $P_D$               | 79              |              |
|   |                     | 40              | A            |
| Continuous Drain Current <sup>(Note 4)</sup>      | $I_D$               | -17             |              |
|   |                     | -14.3           | W            |
| Power Dissipation                                 | $P_D$               | 3               |              |
|   |                     | 2.1             | $^\circ C/W$ |
| Single Pulse Avalanche Energy <sup>(Note 5)</sup> | $E_{AS}$            | 144             | mJ           |
| Operating Junction and Storage Temperature Range  | $T_J, T_{STG}$      | -55~175         | $^\circ C$   |
| Thermal Resistance <sup>(Note 4)</sup>            | Junction to Case    | $R_{\theta JC}$ | 1.9          |
|   | Junction to Ambient | $R_{\theta JA}$ | 50           |

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## Electrical Characteristics ( $T_A=25^\circ\text{C}$ unless otherwise noted)

| PARAMETER                          | SYMBOL                            | TEST CONDITION  | MIN. | TYP.  | MAX.     | UNITS            |
|------------------------------------|-----------------------------------|---|------|-------|----------|------------------|
| <b>Static</b>                      |                                   |   |      |       |          |                  |
| Drain-Source Breakdown Voltage     | $\text{BV}_{\text{DSS}}$          | $\text{V}_{\text{GS}}=0\text{V}, \text{I}_D=-250\mu\text{A}$  | -30  | -     | -        | V                |
| Gate Threshold Voltage             | $\text{V}_{\text{GS}(\text{th})}$ | $\text{V}_{\text{DS}}=\text{V}_{\text{GS}}, \text{I}_D=-250\mu\text{A}$   | -1   | -1.7  | -2.5     |                  |
| Drain-Source On-State Resistance   | $\text{R}_{\text{DS}(\text{on})}$ | $\text{V}_{\text{GS}}=-10\text{V}, \text{I}_D=-20\text{A}$  | -    | 5.1   | 6.4      | $\text{m}\Omega$ |
|                                    |                                   | $\text{V}_{\text{GS}}=-4.5\text{V}, \text{I}_D=-10\text{A}$   | -    | 8     | 10.4     |                  |
| Zero Gate Voltage Drain Current    | $\text{I}_{\text{DSS}}$           | $\text{V}_{\text{DS}}=-30\text{V}, \text{V}_{\text{GS}}=0\text{V}$  | -    | -     | -1       | $\mu\text{A}$    |
| Gate-Source Leakage Current        | $\text{I}_{\text{GSS}}$           | $\text{V}_{\text{GS}}=\pm 25\text{V}, \text{V}_{\text{DS}}=0\text{V}$   | -    | -     | $\pm 10$ | $\mu\text{A}$    |
|                                    |                                   | $\text{V}_{\text{GS}}=\pm 10\text{V}, \text{V}_{\text{DS}}=0\text{V}$   | -    | -     | $\pm 1$  |                  |
| <b>Dynamic</b> <sup>(Note 6)</sup> |                                   |   |      |       |          |                  |
| Total Gate Charge                  | $\text{Q}_g$                      | $\text{V}_{\text{DS}}=-24\text{V}, \text{I}_D=-20\text{A}, \text{V}_{\text{GS}}=-10\text{V}$  | -    | 68    | -        | $\text{nC}$      |
| Gate-Source Charge                 | $\text{Q}_{\text{gs}}$            |   | -    | 9     | -        |                  |
| Gate-Drain Charge                  | $\text{Q}_{\text{gd}}$            |   | -    | 20    | -        |                  |
| Input Capacitance                  | $\text{C}_{\text{iss}}$           | $\text{V}_{\text{DS}}=-25\text{V}, \text{V}_{\text{GS}}=0\text{V}, f=1\text{MHz}$   | -    | 3040  | -        | $\text{pF}$      |
| Output Capacitance                 | $\text{C}_{\text{oss}}$           |   | -    | 427   | -        |                  |
| Reverse Transfer Capacitance       | $\text{C}_{\text{rss}}$           |   | -    | 344   | -        |                  |
| Gate resistance                    | $\text{R}_g$                      | $f=1\text{MHz}$   | -    | 2.2   | -        | $\Omega$         |
| Turn-On Delay Time                 | $\text{t}_{\text{d}(\text{on})}$  | $\text{V}_{\text{DS}}=-24\text{V}, \text{I}_D=-20\text{A}, \text{V}_{\text{GS}}=-10\text{V}, \text{R}_g=3\Omega$<br><small>(Note 2)</small> | -    | 12    | -        | $\text{ns}$      |
| Turn-On Rise Time                  | $\text{t}_r$                      |   | -    | 15    | -        |                  |
| Turn-Off Delay Time                | $\text{t}_{\text{d}(\text{off})}$ |   | -    | 50    | -        |                  |
| Turn-Off Fall Time                 | $\text{t}_f$                      |   | -    | 31    | -        |                  |
| <b>Drain-Source Diode</b>          |                                   |   |      |       |          |                  |
| Diode Forward Current              | $\text{I}_s$                      | $\text{T}_{\text{C}}=25^\circ\text{C}$  | -    | -     | -88      | $\text{A}$       |
| Pulsed Diode Forward Current       | $\text{I}_{\text{SM}}$            |   | -    | -     | -219     |                  |
| Diode Forward Voltage              | $\text{V}_{\text{SD}}$            | $\text{I}_s=-20\text{A}, \text{V}_{\text{GS}}=0\text{V}$  | -    | -0.85 | -1.3     | $\text{V}$       |
| Reverse Recovery Time              | $\text{T}_{\text{rr}}$            | $\text{V}_{\text{GS}}=0\text{V}, \text{I}_s=-20\text{A}$<br>$d\text{I}_{\text{s}}/dt=100\text{A}/\mu\text{s}$                               | -    | 26    | -        | $\text{ns}$      |
| Reverse Recovery Charge            | $\text{Q}_{\text{rr}}$            |   | -    | 16    | -        |                  |

### NOTES :

1. Pulse width  $\leq 300\mu\text{s}$ , Duty cycle  $\leq 2\%$ .
2. Essentially independent of operating temperature typical characteristics.
3. The maximum current rating is package limited.
4.  $\text{R}_{\text{JA}}$  is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. Mounted on a 1 inch<sup>2</sup> with 2oz.square pad of copper.
5. The test condition is  $L=0.5\text{mH}, \text{I}_{\text{AS}}=-24\text{A}, \text{V}_{\text{DD}}=-30\text{V}, \text{V}_{\text{GS}}=-10\text{V}$ , Starting  $\text{T}_{\text{J}}=25^\circ\text{C}$ .
6. Guaranteed by design, not subject to production testing.

# PJD90P03E-AU

## TYPICAL CHARACTERISTIC CURVES

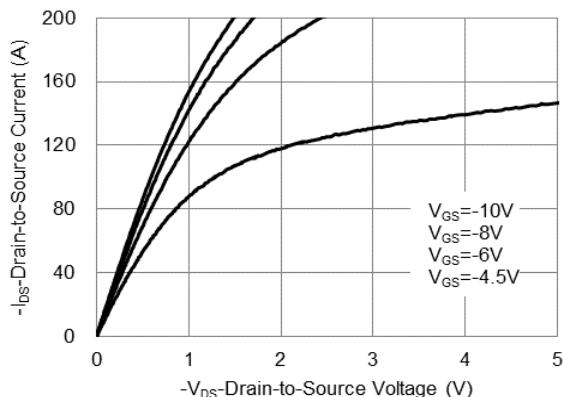


Fig.1 On-Region Characteristics

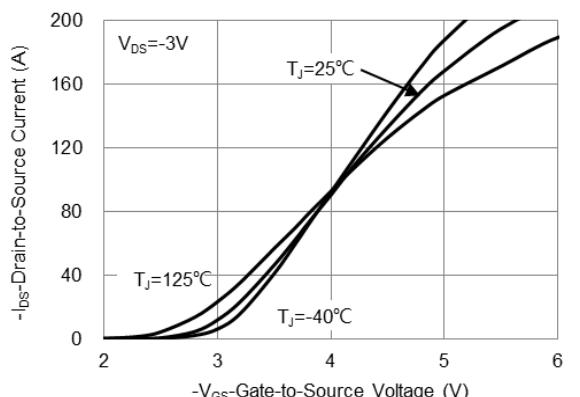


Fig.2 Transfer Characteristics

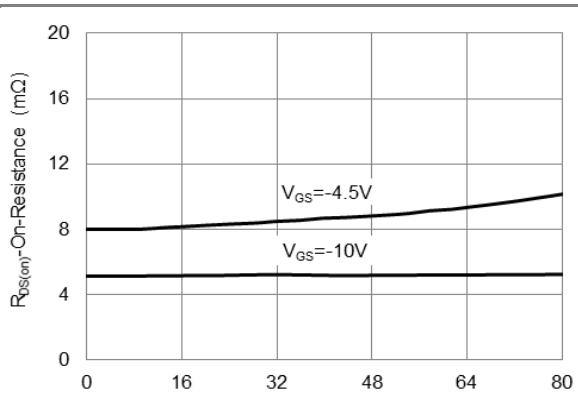


Fig.3 On-Resistance vs. Drain Current

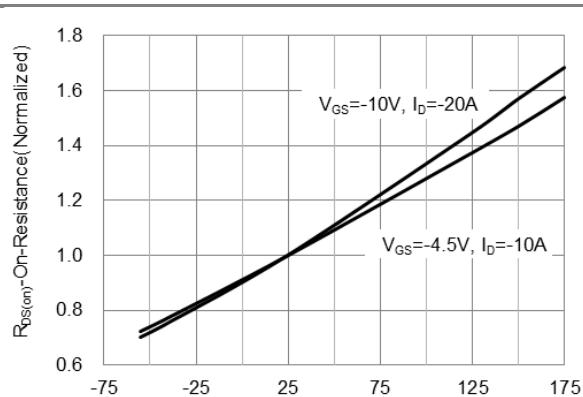


Fig.4 On-Resistance vs. Junction temperature

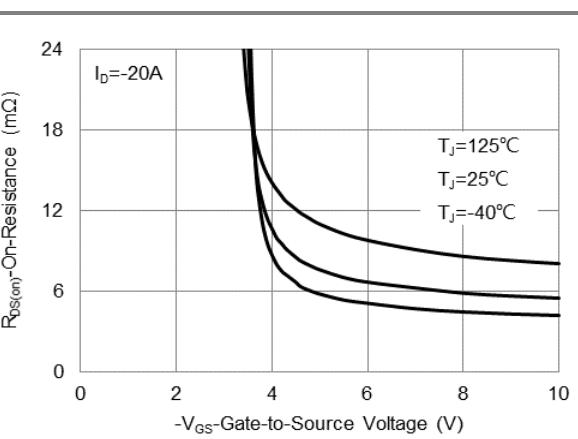


Fig.5 On-Resistance Variation with V<sub>GS</sub>

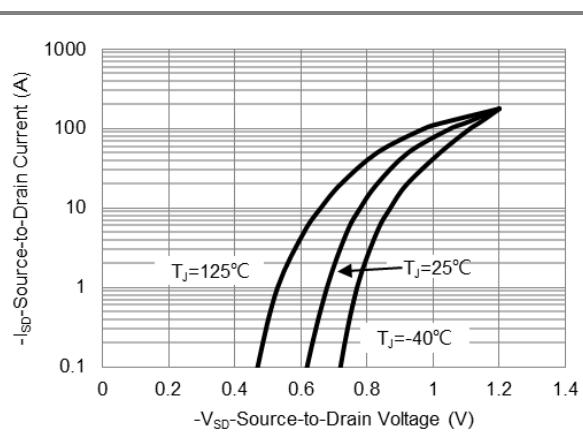


Fig.6 Source-Drain Diode Forward Voltage

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## TYPICAL CHARACTERISTIC CURVES

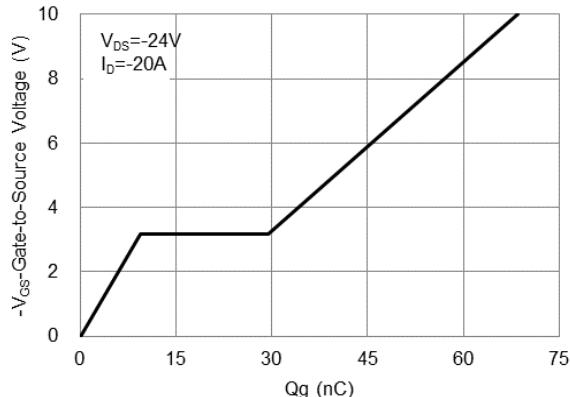


Fig.7 Gate-Charge Characteristics

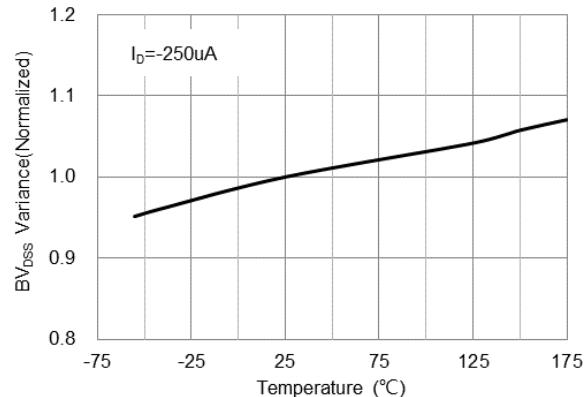


Fig.8 Breakdown Voltage Variation vs. Temperature

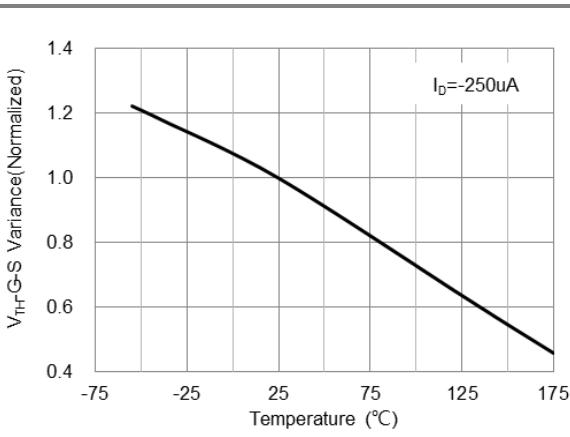


Fig.9 Threshold Voltage Variation with Temperature

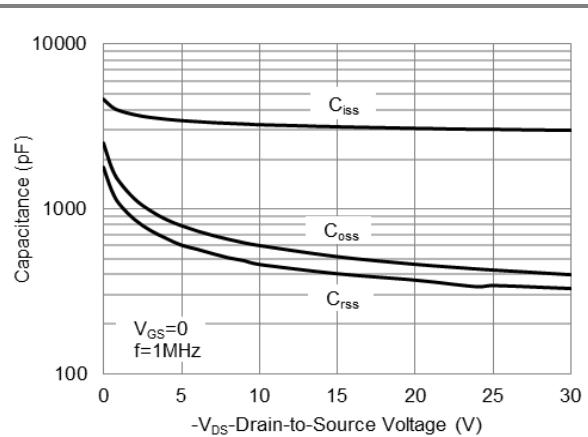


Fig.10 Capacitance vs. Drain-Source Voltage

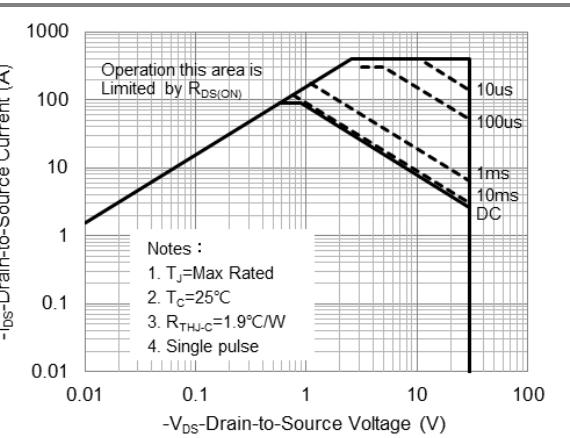


Fig.11 Maximum Safe Operating Area

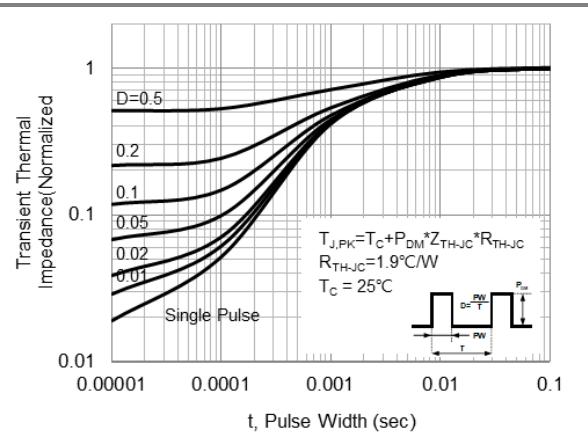


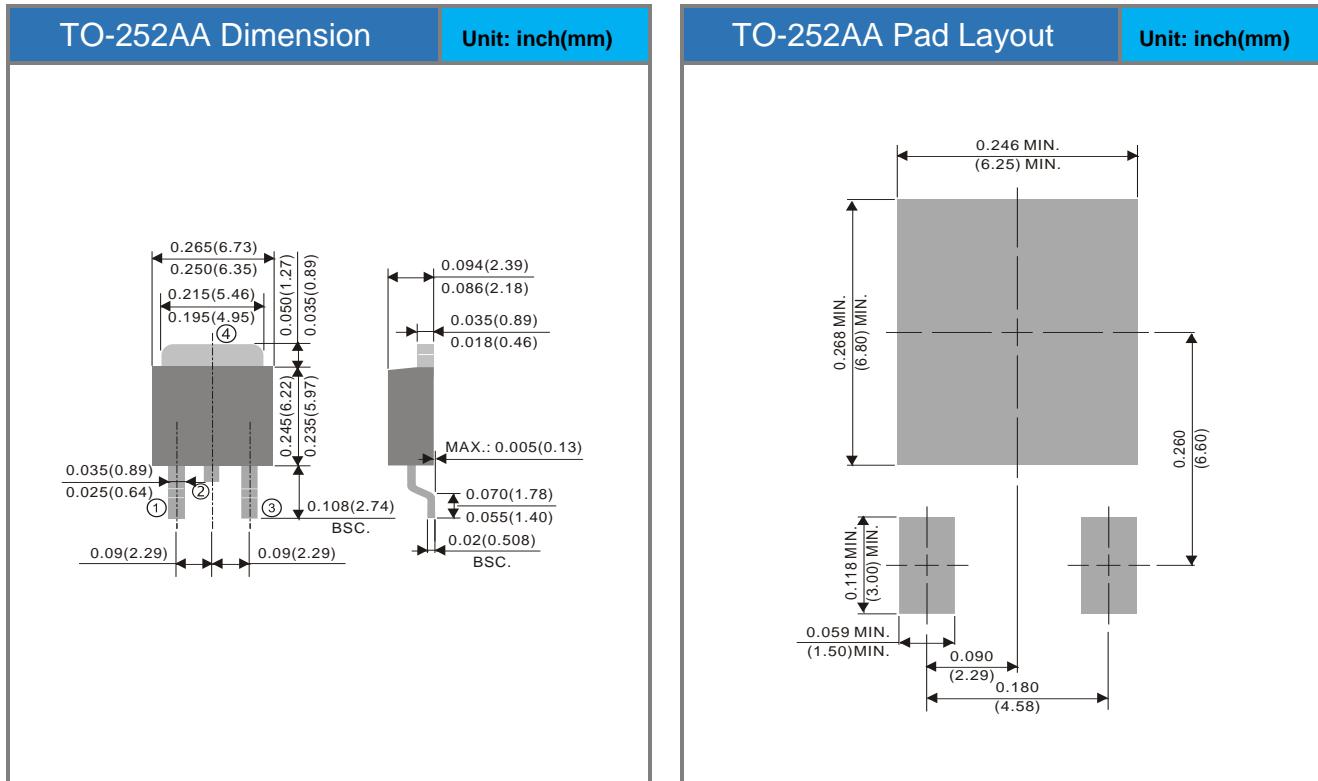
Fig.12 Normalized Transient Thermal Impedance

PJD90P03E-AU

## **Product and Packing Information**

| Part No.     | Package Type | Packing Type      | Marking |
|--------------|--------------|-------------------|---------|
| PJD90P03E-AU | TO-252AA     | 3K pcs / 13" reel | D90P03E |

## Packaging Information & Mounting Pad Layout



## **PJD90P03E-AU**

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